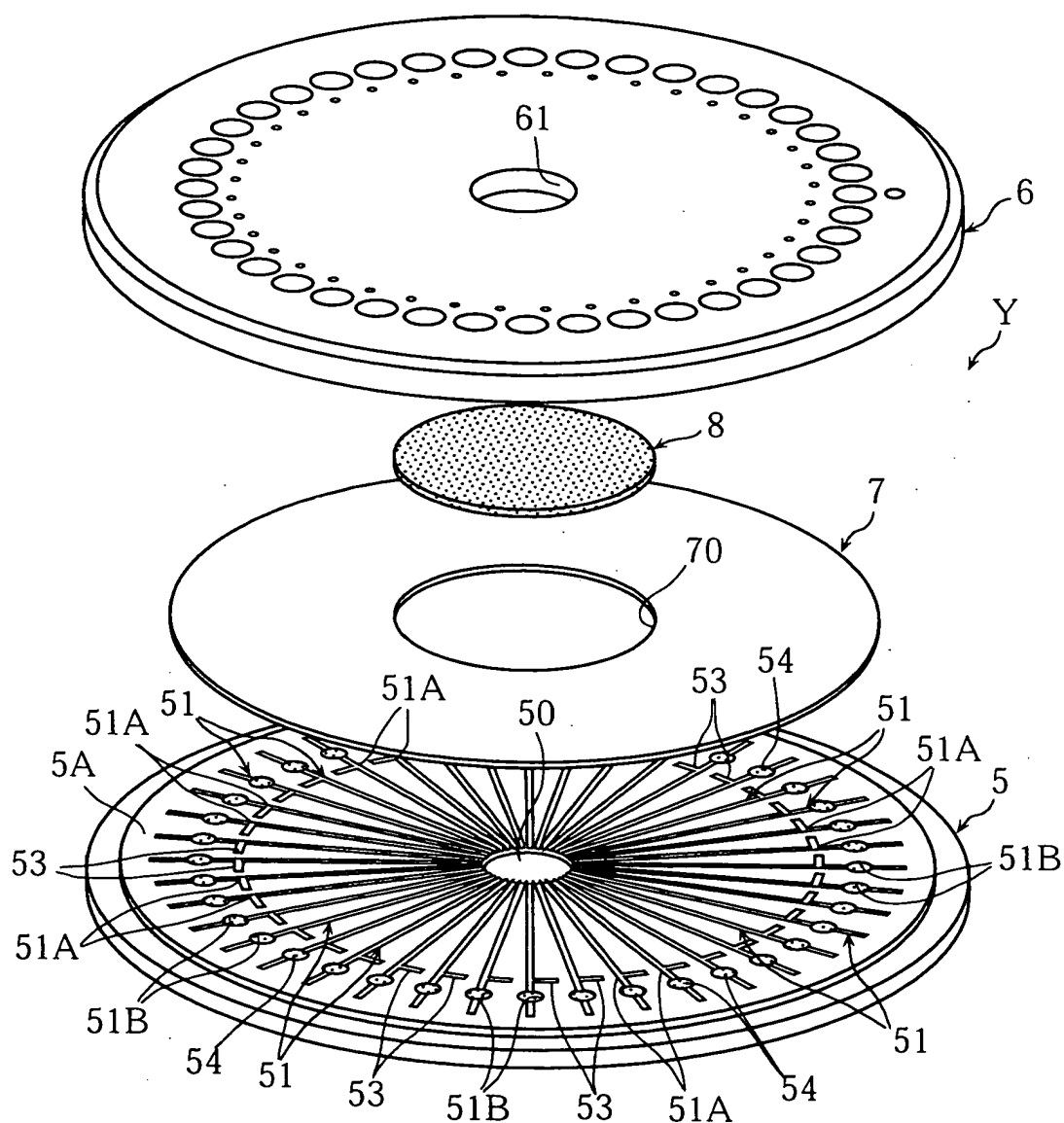


[illegible]

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FIG. 4



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FIG. 6

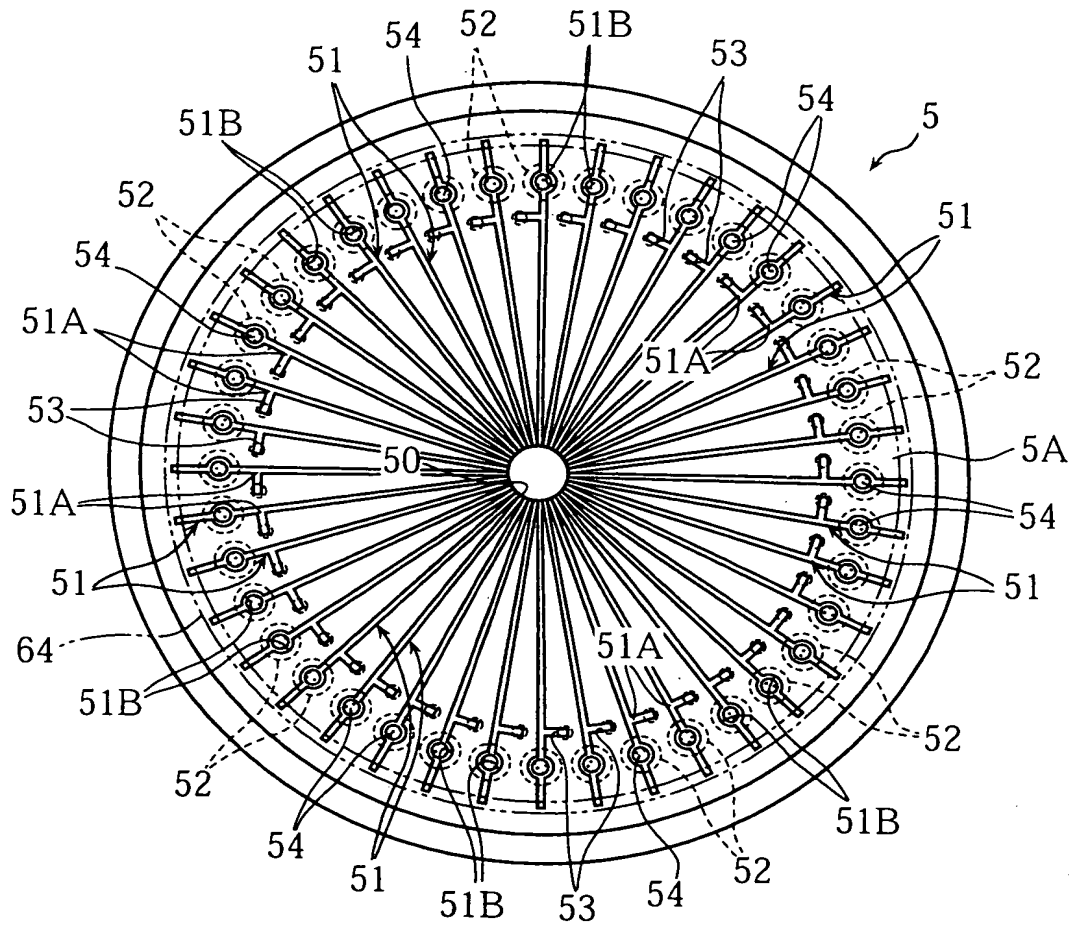


FIG. 7

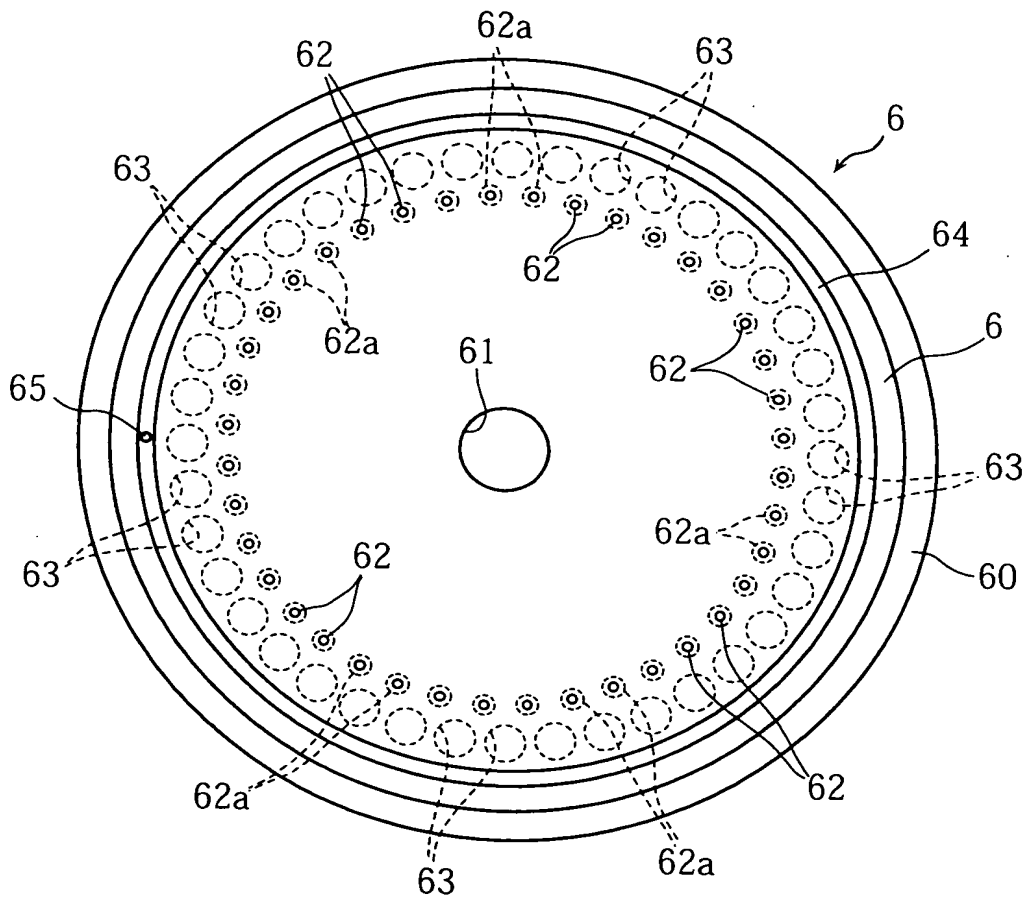
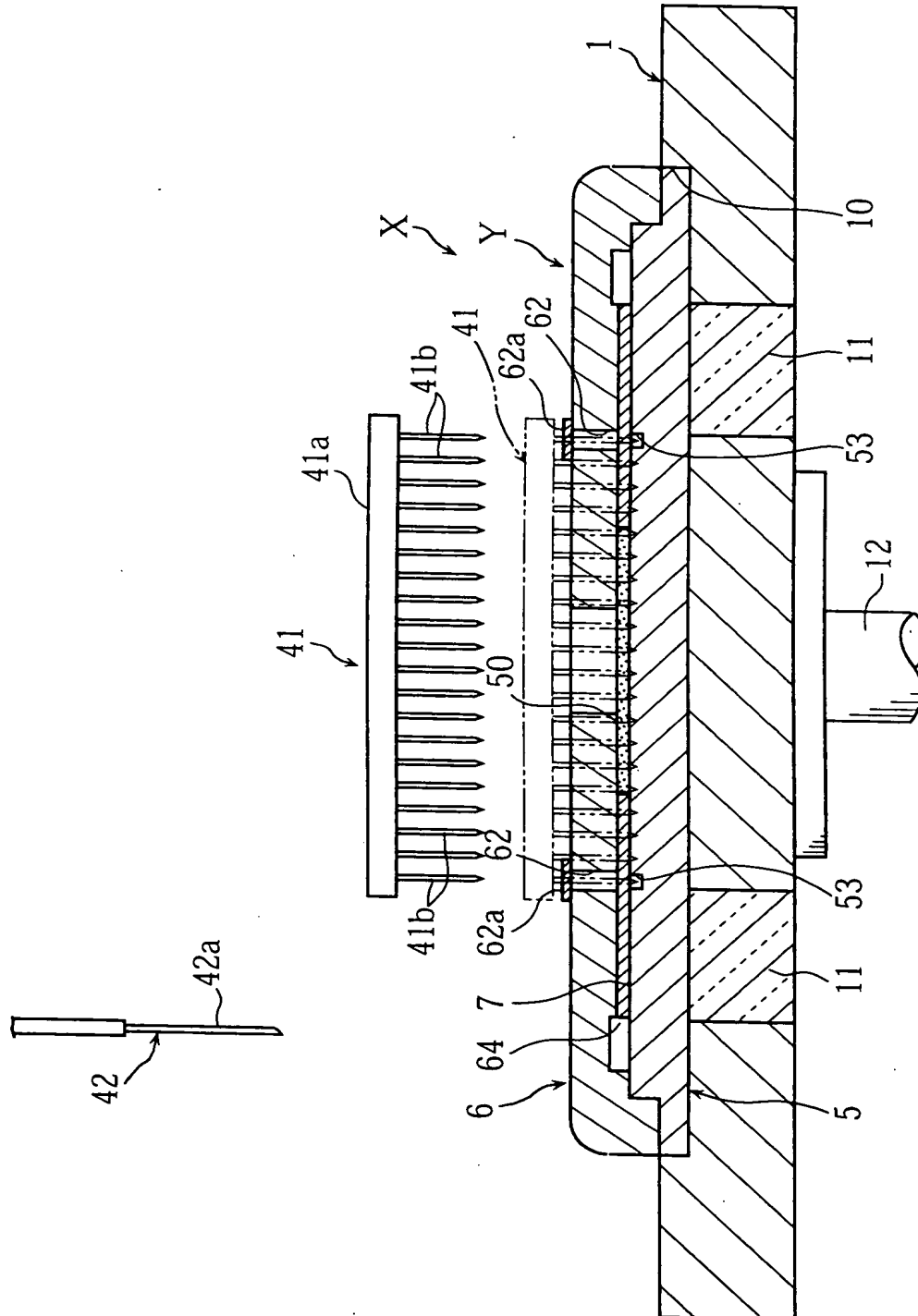


FIG. 8



A detailed cross-sectional diagram of a semiconductor device. The device consists of several stacked layers. At the top is a layer labeled 1. Below it are various functional layers and structures, including regions labeled 6, 7, 8, 9, 10, 11, 12, 13, 14, 15, 16, 17, 18, 19, 20, 21, 22, 23, 24, 25, 26, 27, 28, 29, 30, 31, 32, 33, 34, 35, 36, 37, 38, 39, 40, 41, 42, 43, 44, 45, 46, 47, 48, 49, 50, 51, 52, 53, 54, 55, 56, 57, 58, 59, 60, 61, 62, 63, 64, 65, 66, 67, 68, 69, 70, 71, 72, 73, 74, 75, 76, 77, 78, 79, 80, 81, 82, 83, 84, 85, 86, 87, 88, 89, 90, 91, 92, 93, 94, 95, 96, 97, 98, 99, 100. The diagram shows a complex arrangement of these layers, with some regions being doped or having different material properties than others. Arrows indicate specific directions or features within the device.

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FIG.10A

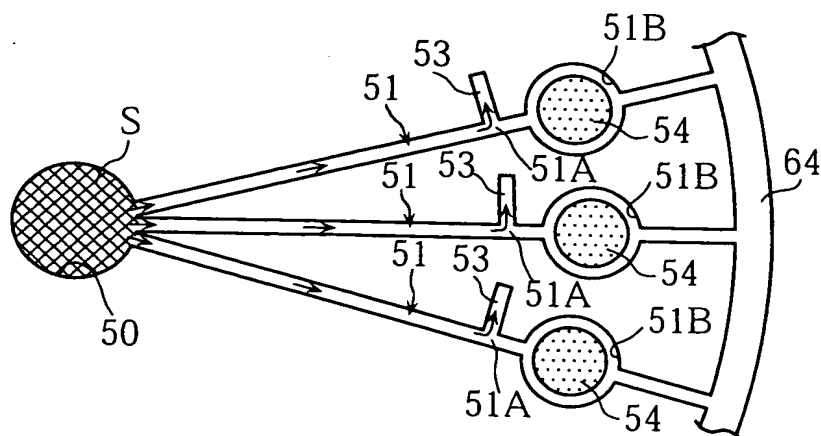


FIG.10B

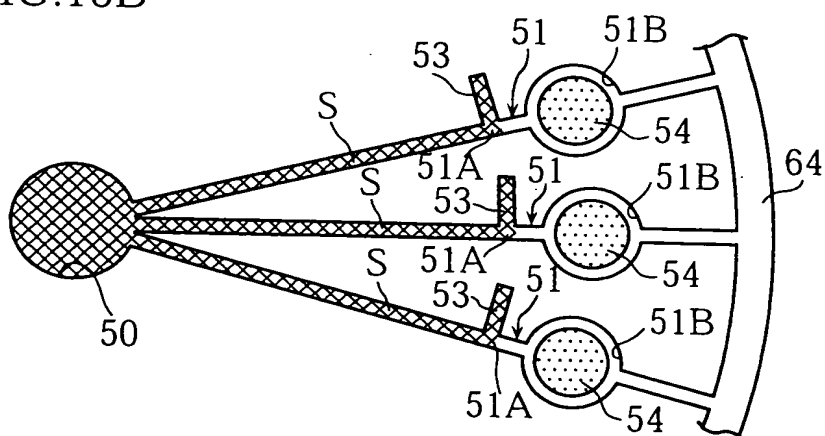
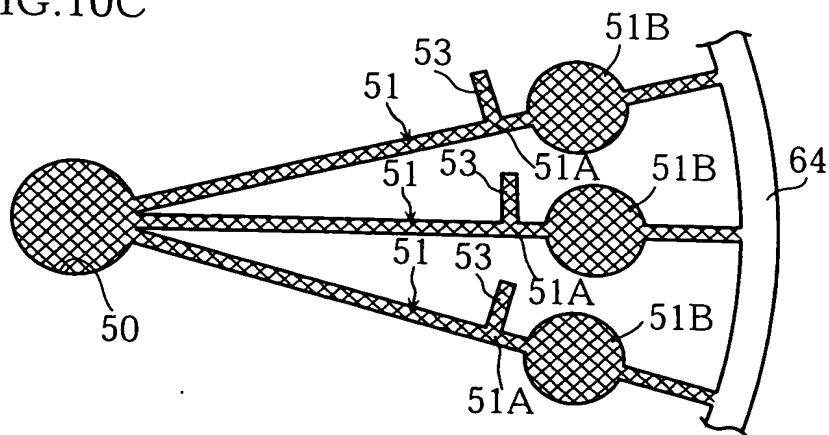


FIG.10C



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FIG.11

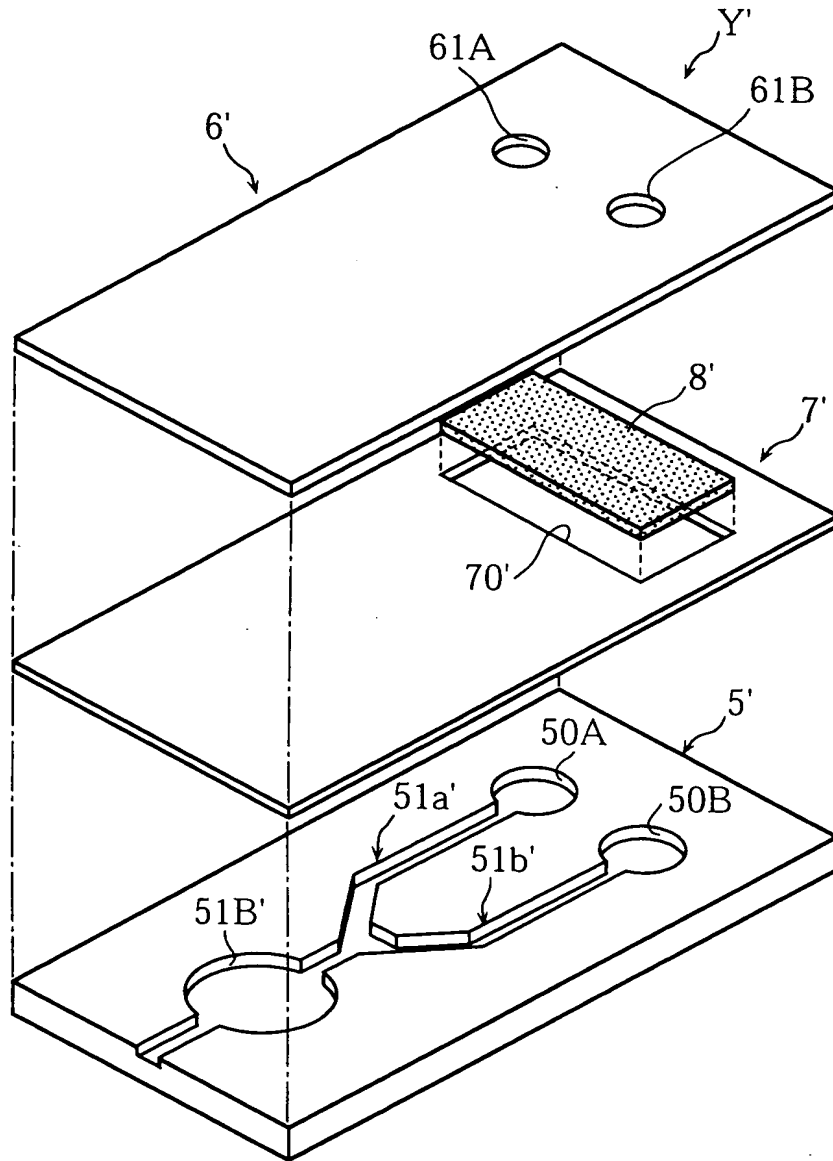
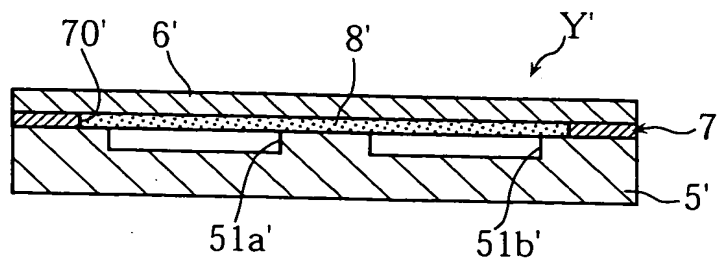


FIG.12



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FIG.13
PRIOR ART

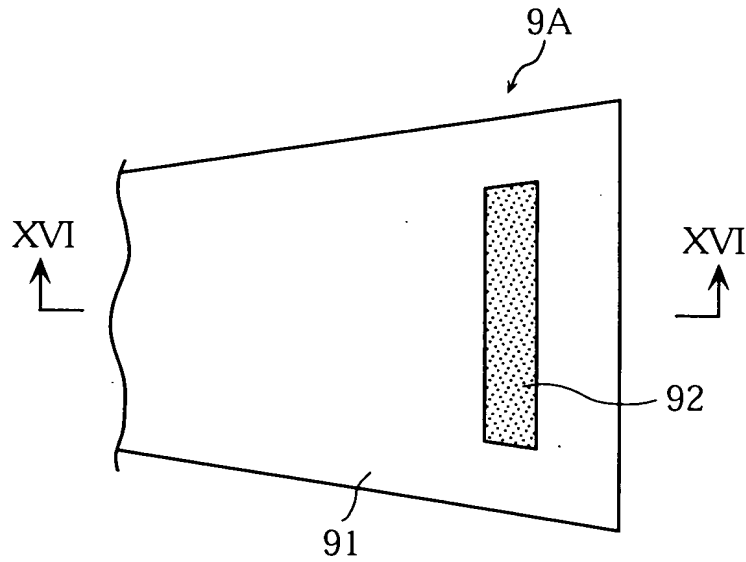
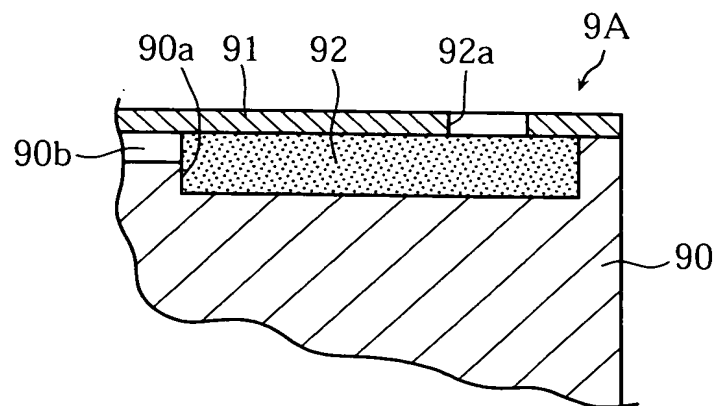


FIG.14
PRIOR ART



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FIG. 15
PRIOR ART

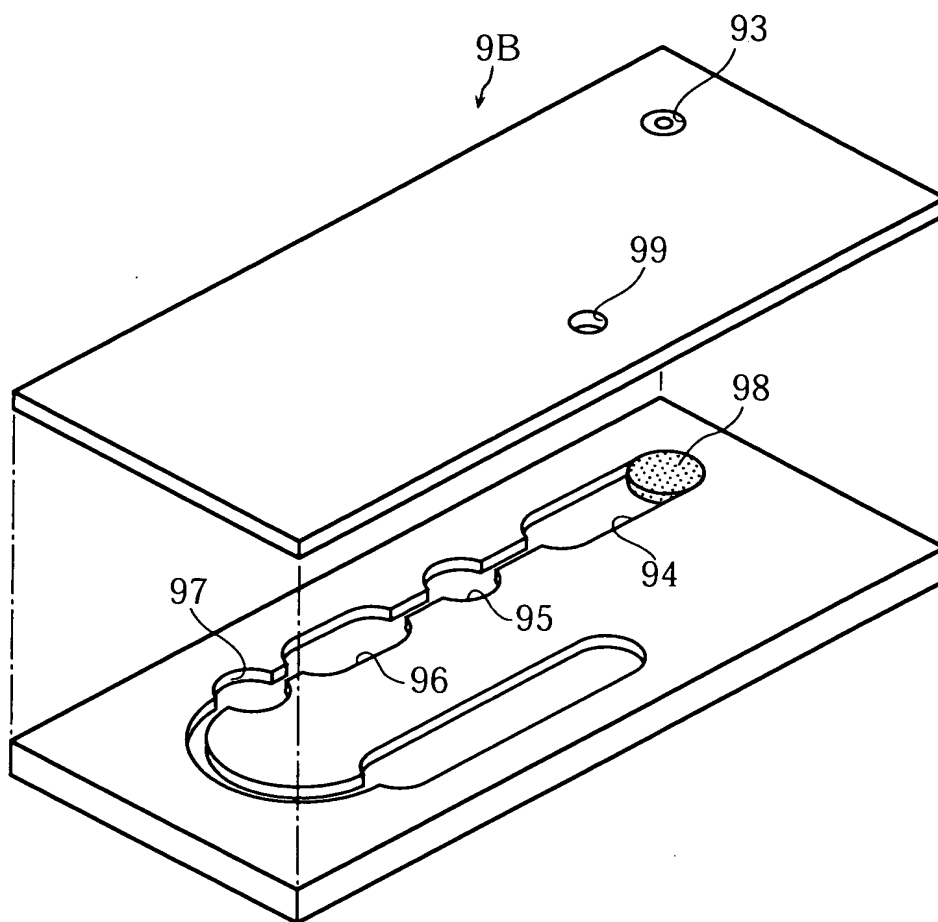


FIG. 16
PRIOR ART

